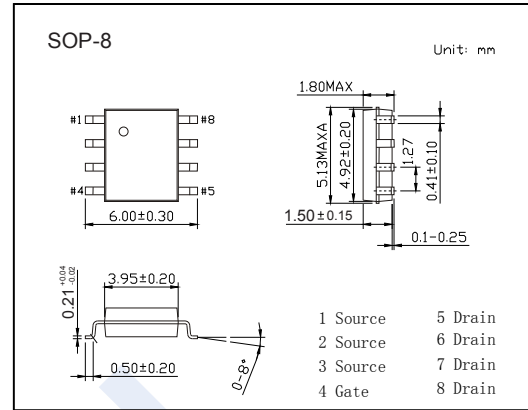
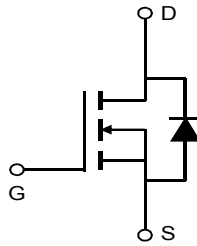


N-Channel MOSFET

AO4264 (KO4264)

■ Features

- $V_{DS} (V) = 60V$
- $I_D = 12 A (V_{GS} = 10V)$
- $R_{DS(ON)} < 11m\Omega (V_{GS} = 10V)$
- $R_{DS(ON)} < 13.5m\Omega (V_{GS} = 4.5V)$

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	V_{DS}	60	V	
Gate-Source Voltage	V_{GS}	± 20		
VDS Spike @ 10us	V_{SPIKE}	72		
Continuous Drain Current	I_D	$T_A=25^\circ C$	12	A
		$T_A=70^\circ C$	9	
Pulsed Drain Current	I_{DM}	48		
Avalanche Current	I_{AS}	36		
Avalanche Energy	$L=0.1mH$	E_{AS}	65	mJ
Power Dissipation	P_D	$T_A=25^\circ C$	3.1	W
		$T_A=70^\circ C$	2	
Thermal Resistance.Junction- to-Ambient	R_{thJA}	$t \leq 10s$	40	$^\circ C/W$
		Steady-State	75	
Thermal Resistance.Junction- to-Lead	R_{thJL}	24		
Junction Temperature	T_J	150	$^\circ C$	
Storage Temperature Range	T_{stg}	-55 to 150		

N-Channel MOSFET

AO4264 (KO4264)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 uA, V _{GS} =0V	60			V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	uA	
		V _{DS} =60V, V _{GS} =0V, T _J =55°C			5		
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1.4		2.5	V	
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =12A			11	mΩ	
		V _{GS} =10V, I _D =12A T _J =125°C			19		
		V _{GS} =4.5V, I _D =10A			13.5		
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =12A		50		S	
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =30V, f=1MHz		2007		pF	
Output Capacitance	C _{oss}			177			
Reverse Transfer Capacitance	C _{rss}			12.5			
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.6		1.8	Ω	
Total Gate Charge (10V)	Q _g	V _{GS} =10V, V _{DS} =30V, I _D =12A		25.5	40	nC	
Total Gate Charge (4.5V)				11	20		
Gate Source Charge			Q _{gs}		5.5		
Gate Drain Charge			Q _{gd}		2.5		
Turn-On DelayTime	t _{d(on)}	V _{GS} =10V, V _{DS} =15V, R _L =1.25Ω, R _{GEN} =3Ω		8.5		ns	
Turn-On Rise Time	t _r			3.5			
Turn-Off DelayTime	t _{d(off)}			27			
Turn-Off Fall Time	t _f			3			
Body Diode Reverse Recovery Time	t _{rr}	I _F = 12A, di/dt= 500A/us		15		nC	
Body Diode Reverse Recovery Charge	Q _{rr}			55			
Maximum Body-Diode Continuous Current	I _S				4	A	
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V			1	V	

Note : The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

■ Marking

Marking	4264 KC****
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N-Channel MOSFET AO4264 (KO4264)

■ Typical Characteristics

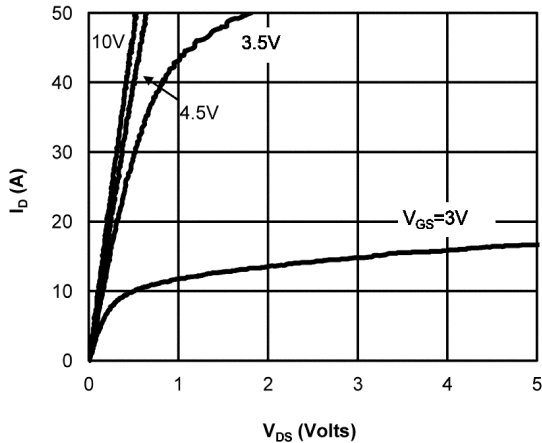


Figure 1: On-Region Characteristics (Note E)

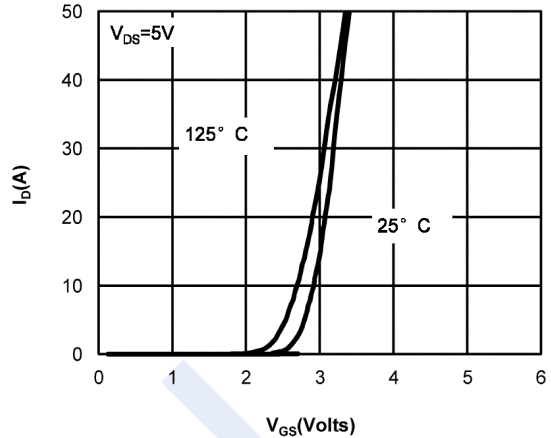


Figure 2: Transfer Characteristics (Note E)

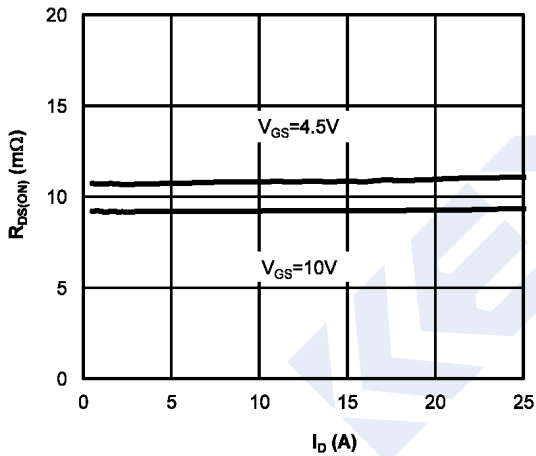


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

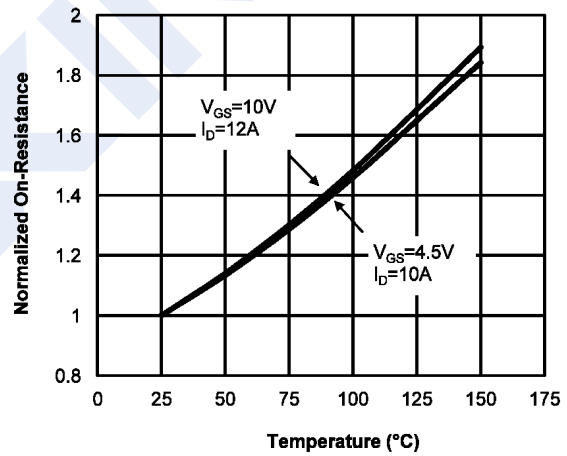


Figure 4: On-Resistance vs. Junction Temperature (Note E)

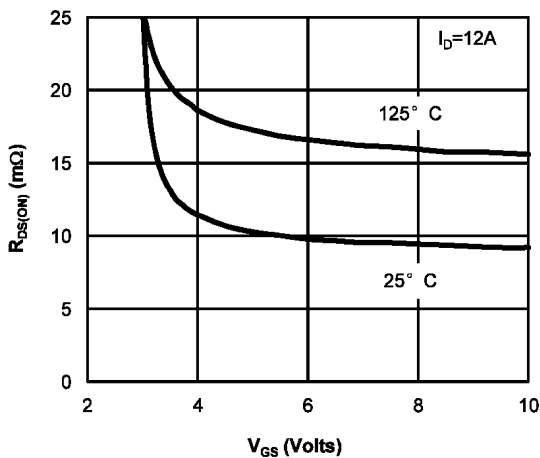


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

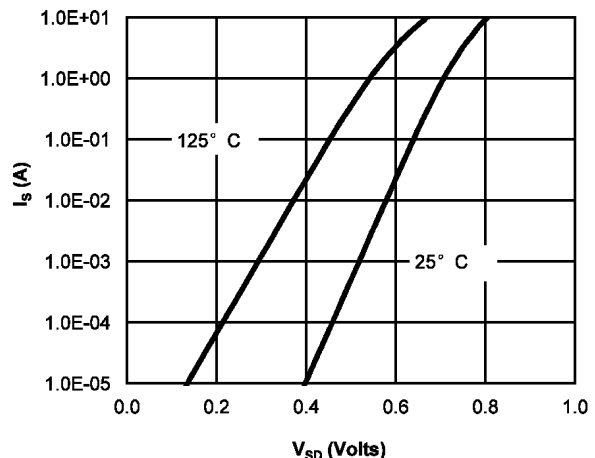


Figure 6: Body-Diode Characteristics (Note E)

N-Channel MOSFET

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■ Typical Characteristics

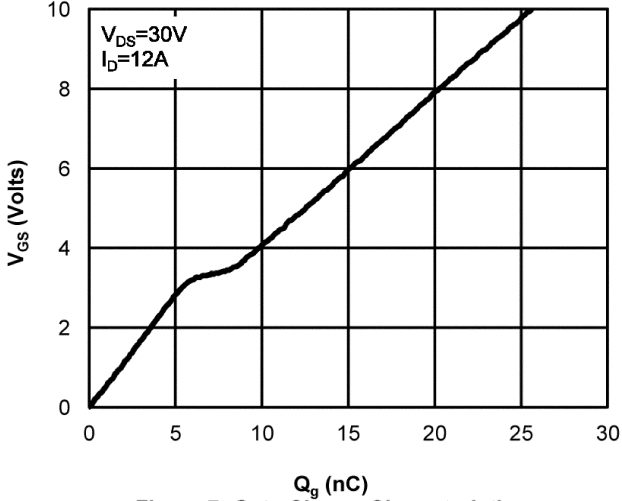


Figure 7: Gate-Charge Characteristics

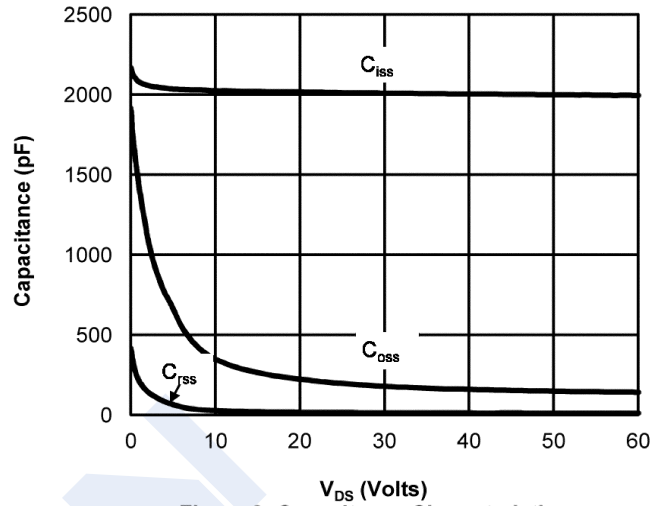


Figure 8: Capacitance Characteristics

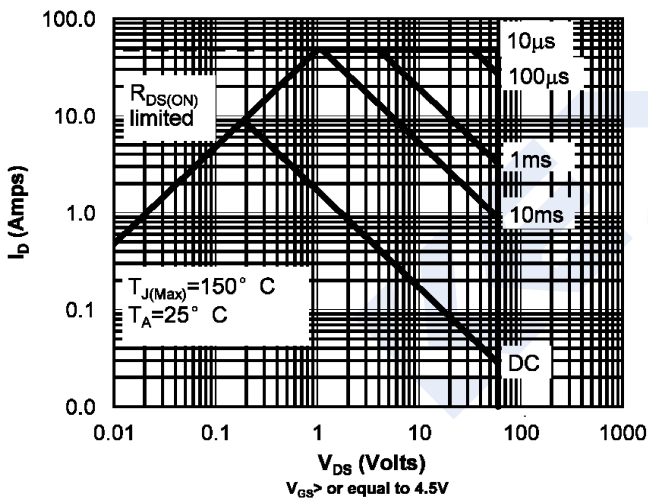


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

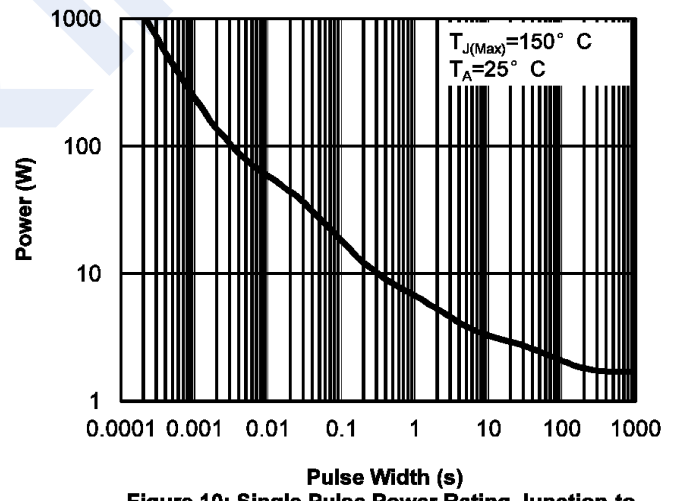


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

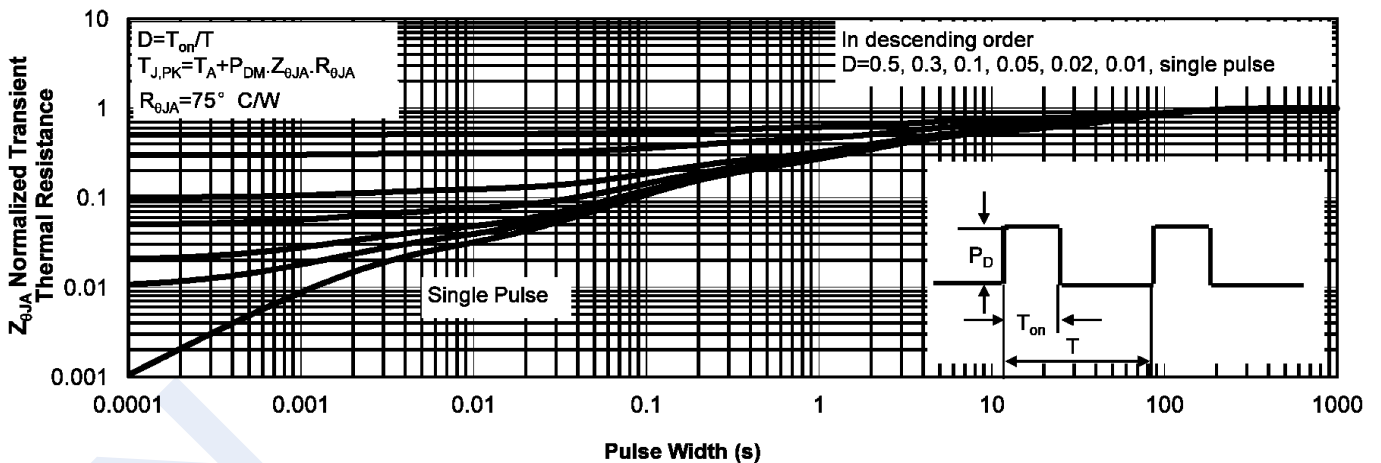


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)